

## CLAIMS

1. A Mg-based ferrite material having a composition of formula (1):



5 wherein a, b, and c satisfy

$$0.10 \leq b/(b+c/2) \leq 0.85 \text{ and}$$

$$0 \leq R(\text{Ca}) \leq 0.10,$$

wherein R(Ca) is expressed as

$$R(\text{Ca}) = a \times \text{Fw}(\text{CaO}) / ( a \times \text{Fw}(\text{CaO}) + b \times \text{Fw}(\text{MgO}) + (c/2) \times \text{Fw}(\text{Fe}_2\text{O}_3) )$$

(Fw(A): formula weight of A) ; and

d is determined by oxidation numbers of Ca, Mg and Fe;

wherein said Mg-based ferrite material has a saturation magnetization in the range of 30-80 emu/g,

15 wherein said Mg-based ferrite material has a dielectric breakdown voltage in the range of 1.0-5.0 kV.

2. A Mg-based ferrite material as claimed in claim 1, wherein b and c satisfy  $0.30 \leq b/(b+c/2) \leq 0.70$ .

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3. A Mg-based ferrite material as claimed in claim 1 or claim 2,

wherein said Mg-based ferrite material has an average particle diameter in the range of 0.01-150  $\mu\text{m}$ .

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4. An electrophotographic development carrier, which comprises a Mg-based ferrite material according to any of claims 1-3.

5. An electrophotographic development carrier, which comprises a Mg-based ferrite material according to any of claims 1-3,

5 wherein said Mg-based ferrite material is coated with resin.

6. An electrophotographic developer, which comprises an electrophotographic development carrier according to claim  
10 4 or 5, and a toner.

7. An electrophotographic developer as claimed in claim 6,

wherein the ratio of the toner to the carrier by  
15 weight is in the range of 2-40 wt%.

8. A process for producing a Mg-based ferrite carrier according to any of claims 1-3, which comprises the steps of:

- 20 i) mixing raw materials;
- ii) sintering the mixed raw materials to grow particles, wherein a maximum temperature is in the range of 800-1500 °C; and
- iii) heating the sintered raw materials under an  
25 oxygen-containing atmosphere to condition properties of the particles, wherein a maximum temperature in the range of 300-1000 °C;

9. A process for producing a Mg-based ferrite carrier as claimed in claim 8,

wherein an oxygen concentration of the atmosphere in step iii) is higher than that in step ii).

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10. A process for producing a Mg-based ferrite carrier as claimed in claim 8 or claim 9,

wherein the atmosphere in step iii) is an inert gas atmosphere having an oxygen concentration of 0.05-25.0 vol.% on the basis of the total amount of the gases contained in the atmosphere.

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11. A process for producing a Mg-based ferrite carrier as claimed in any of claims 8-10,

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wherein the atmosphere in step ii) is an inert gas atmosphere having an oxygen concentration of 0.001-10.0 vol.% on the basis of the total amount of the gases contained in the atmosphere.

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12. A process for producing a Mg-based ferrite carrier as claimed in any of claims 8-11,

wherein step i) of mixing raw materials comprises steps of:

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preparing a slurry containing a Mg-containing compound and a Fe-containing compound; and drying the slurry for granulation.

13. A process for producing a Mg-based ferrite carrier

according to claim 12,

wherein the slurry comprising a Mg-containing compound and a Fe-containing compound further comprises a Ca-containing compound.

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14. A process for producing a Mg-based ferrite carrier according to claim 12 or 13,

wherein the slurry comprising a Mg-containing compound and a Fe-containing compound further comprises a binder,

10 wherein the content of the binder is in the range of 0.1-5 % by weight, based on the total amount of the raw materials in the slurry.

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